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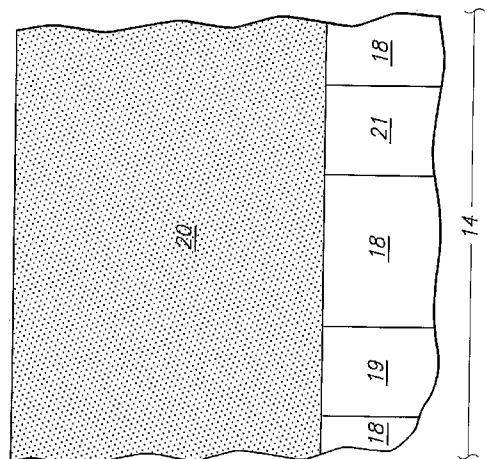
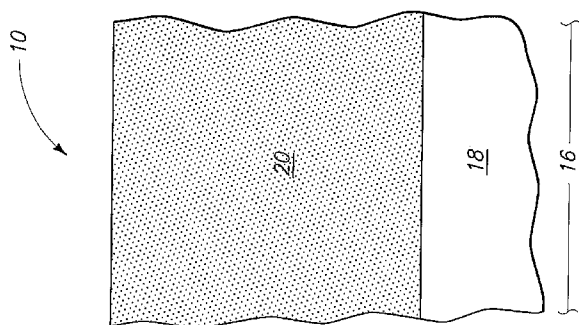
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(54) Title: METHODS OF FORMING PLURALITIES OF CAPACITORS



(57) Abstract: The invention includes methods of forming pluralities of capacitors. In one implementation, a method of forming a plurality of capacitors includes providing a plurality of capacitor electrodes within a capacitor array area over a substrate. The capacitor electrodes comprise outer lateral sidewalls. The plurality of capacitor electrodes is supported at least in part with a retaining structure (40) which engages the outer lateral sidewalls. The retaining structure (40) is formed at least in part by etching a layer (36) of material which is not masked anywhere within the capacitor array area to form said retaining structure. The plurality of capacitor electrodes is incorporated into a plurality of capacitors .



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